

CMP045N10/CMB045N10/CMI045N10/CMF045N10

100V, 3.8mΩ typ., 160A N-Channel MOSFET

General Description

This N-Channel MOSFET is produced using Cmos's advance SGT process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Product Summary

BVDSS	R _{DS(on)} max.	ID
100V	4.3mΩ	160A

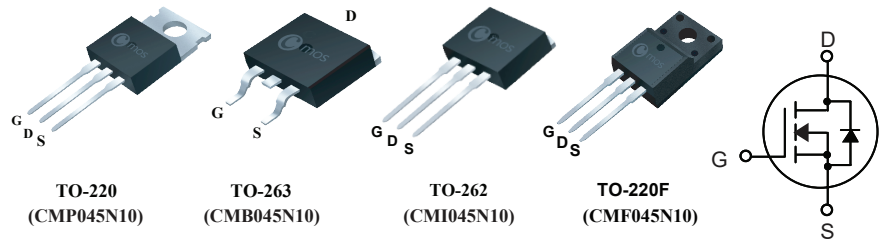
Applications

- Motor control and drive
- Battery management

Features

- Low On-Resistance
- 100% avalanche tested
- RoHS Compliant

TO-220/263/262/220F Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	220/263/262	220F	Units
V _{DS}	Drain-Source Voltage	100		V
V _{GS}	Gate-Source Voltage	±20		V
I _D @T _C =25°C	Continuous Drain Current	160	160*	A
I _D @T _C =100°C	Continuous Drain Current	112	112*	A
I _{DM}	Pulsed Drain Current	640	640*	A
EAS	Single Pulse Avalanche Energy (Note 1)	1322		mJ
P _D @T _C =25°C	Total Power Dissipation	260	40	W
T _{STG}	Storage Temperature Range	-55 to 150		°C
T _J	Operating Junction Temperature Range	-55 to 150		°C

* Drain current limited by maximum junction temperature.

Thermal Data

Symbol	Parameter	220/263/262	220F	Unit
R _{θJA}	Thermal Resistance Junction-ambient Max.	62.5	62.5	°C/W
R _{θJC}	Thermal Resistance Junction-case Max.	0.48	3.13	°C/W

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	100	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$, $I_D=40A$	---	3.8	4.3	mΩ
		$V_{GS}=4.5V$, $I_D=40A$	---	4.9	5.8	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1	---	3	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=100V$, $V_{GS}=0V$	---	---	1	uA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=10V$, $I_D=20A$	---	44	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	2.0	---	Ω
Q_g	Total Gate Charge	$V_{DS}=50V$, $I_D=40A$ $V_{GS}=10V$	---	60	---	nC
Q_{gs}	Gate-Source Charge		---	16	---	
Q_{gd}	Gate-Drain Charge		---	11	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=50V$ $R_{G_ext}=3\Omega$, $V_{GS}=10V$	---	14	---	ns
T_r	Rise Time		---	42	---	
$T_{d(off)}$	Turn-Off Delay Time		---	46	---	
T_f	Fall Time		---	19	---	
C_{iss}	Input Capacitance	$V_{DS}=25V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	3700	---	pF
C_{oss}	Output Capacitance		---	1600	---	
C_{rss}	Reverse Transfer Capacitance		---	100	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Diode continuous forward current	$V_G=V_D=0V$, Force Current	---	---	160	A
$I_{S,pulse}$	Diode pulse current		---	---	640	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_F=40A$, $T_J=25^{\circ}\text{C}$	---	0.85	1.2	V

Note :

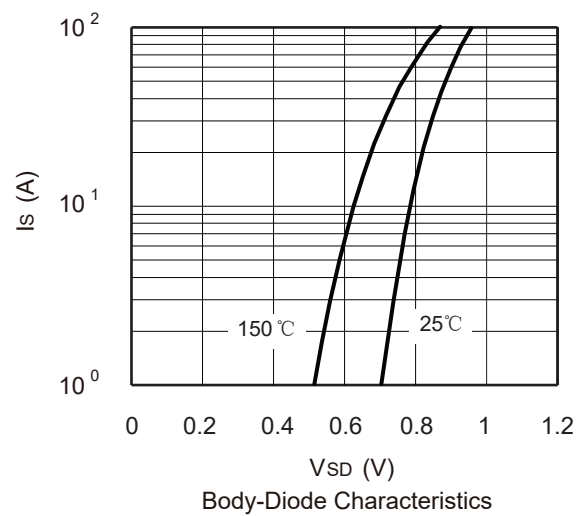
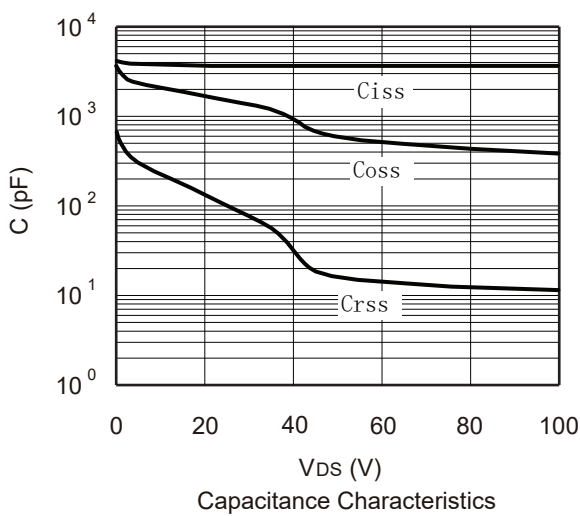
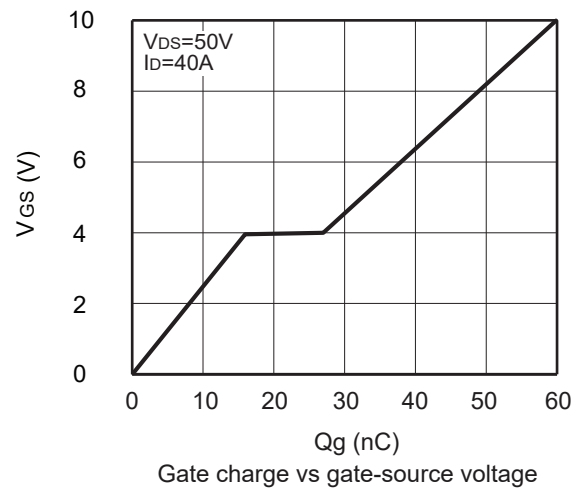
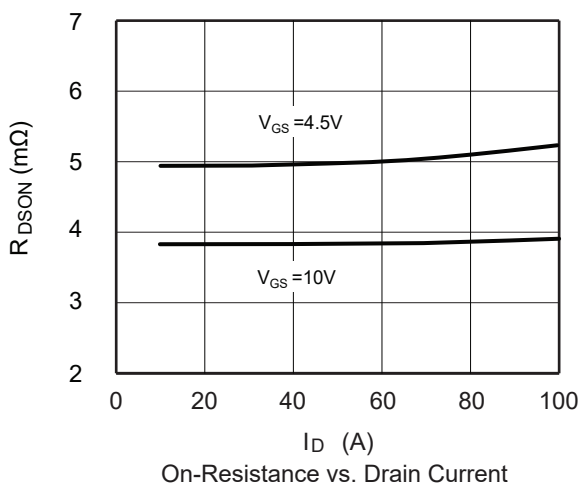
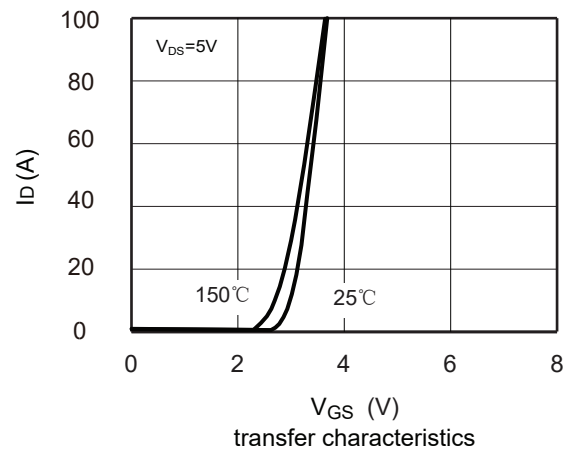
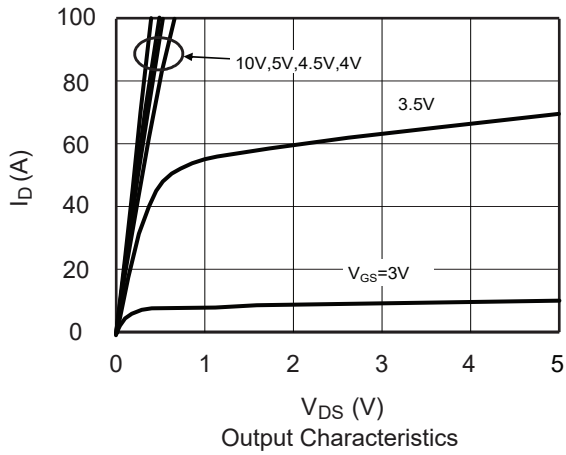
1.The EAS data shows Max. rating .The test condition is $V_{DS}=80V$, $V_{GS}=10V$, $L=5\text{mH}$, $I_{AS}=23A$.

This product has been designed and qualified for the consumer market.

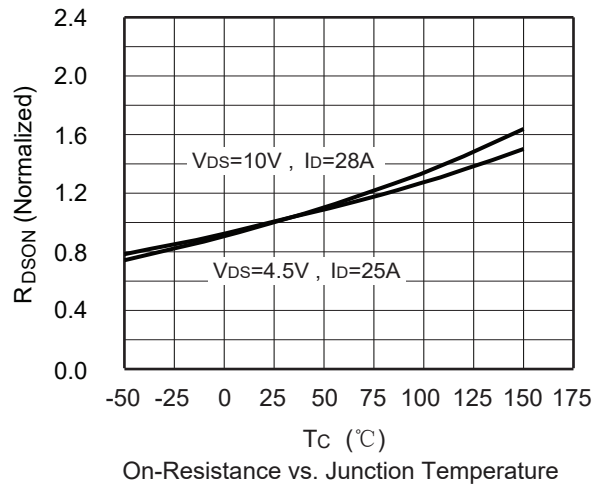
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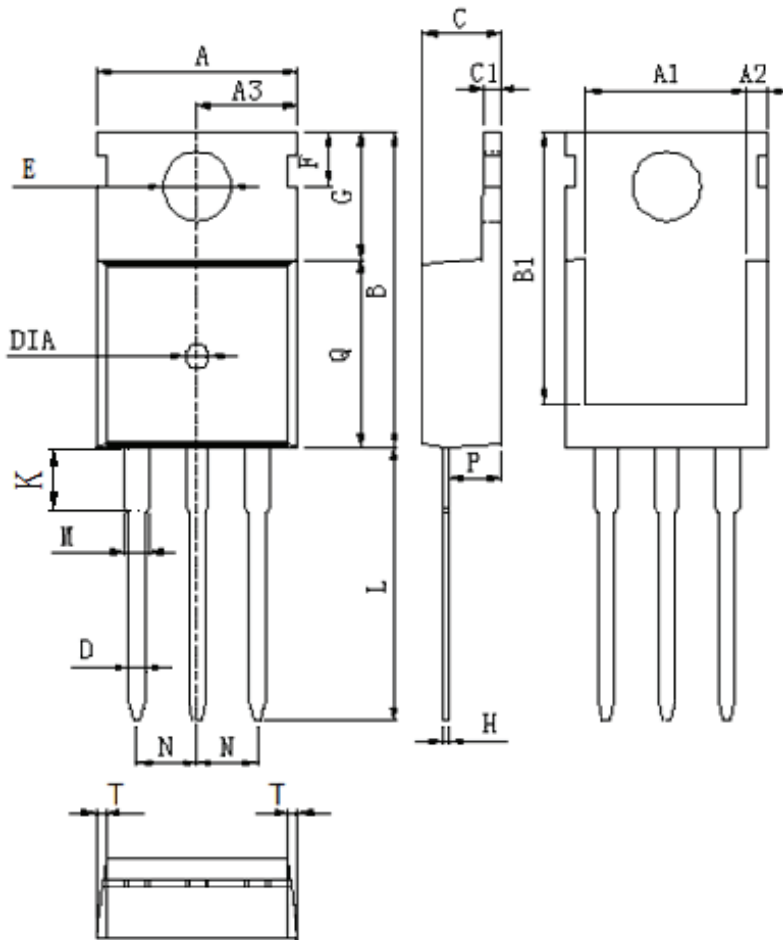
Cmos reserves the right to improve product design ,functions and reliability without notice.Please refer to the latest version of specification.

Typical Characteristics

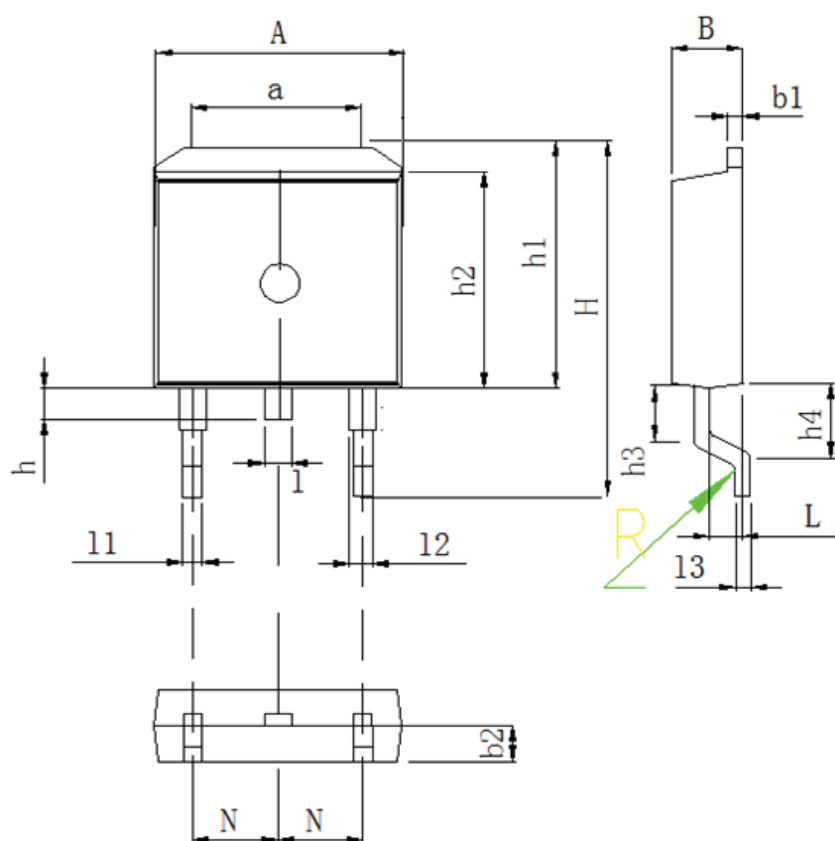


Characteristics

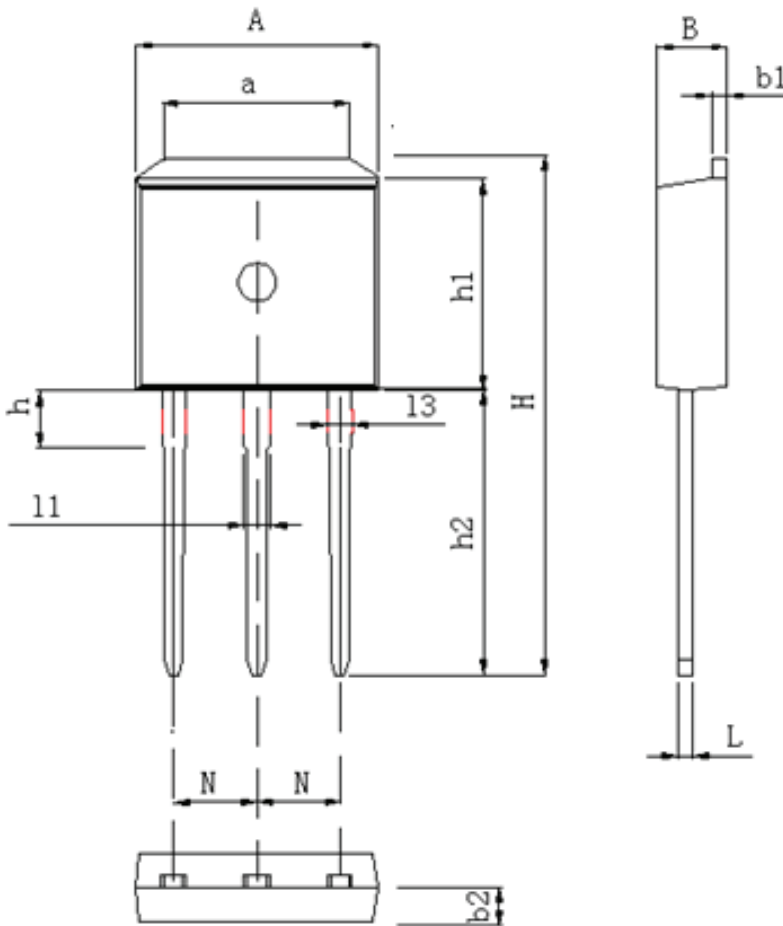


Package Dimension
TO-220
Unit :mm


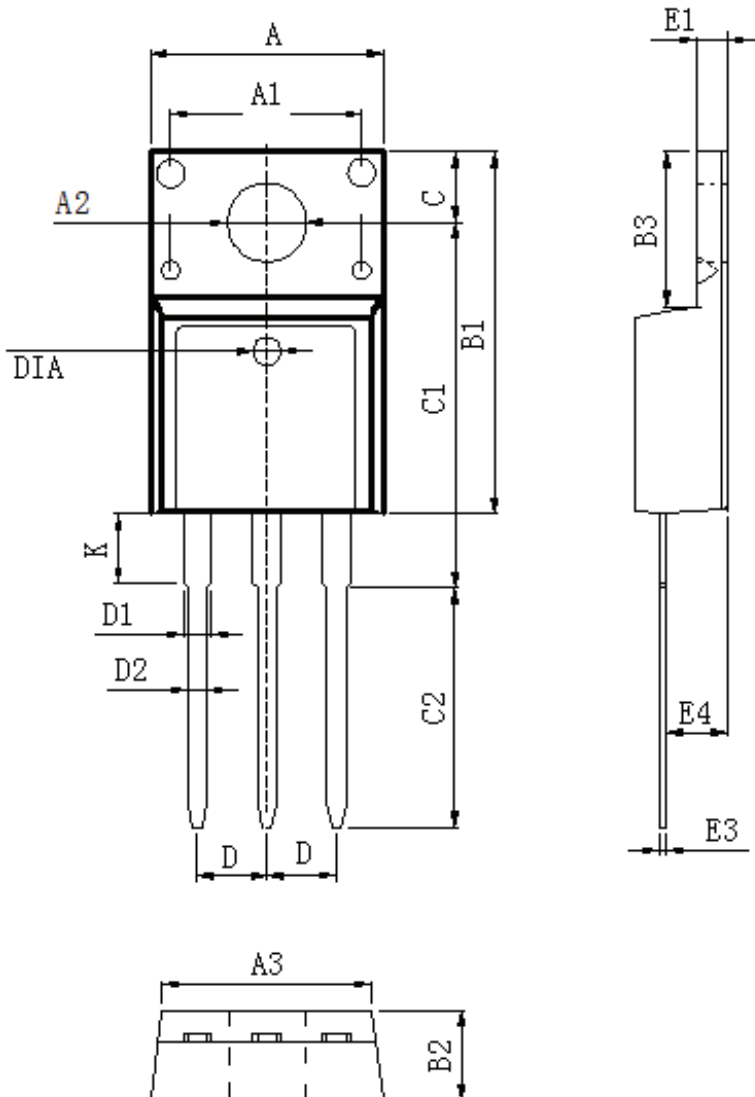
DIM	MILLIMETERS
A	10.0±0.3
A1	8.64±0.2
A2	1.15±0.1
A3	5.0±0.2
B	15.8±0.4
B1	13.2±0.3
C	4.56±0.1
C1	1.3±0.2
D	0.8±0.2
E	3.6±0.2
F	2.95±0.3
G	6.5±0.3
H	0.5±0.1
K	3.1±0.2
L	13.2±0.4
M	1.25±0.1
N	2.54±0.1
P	2.4±0.3
Q	9.0±0.3
T	W:0.35
DIA	⊙1.5(deep 0.2)

Package Dimension
TO-263
Unit :mm


DIM	MILLIMETERS
A	9.8 ± 0.2
a	7.4 ± 0.4
B	4.5 ± 0.2
b1	1.3 ± 0.05
b2	2.4 ± 0.2
H	15.5 ± 0.3
h	1.54 ± 0.2
h1	10.5 ± 0.2
h2	9.2 ± 0.1
h3	1.54 ± 0.2
h4	2.7 ± 0.2
L	2.4 ± 0.2
1	1.3 ± 0.1
11	0.8 ± 0.1
12	1.3 ± 0.1
13	0.5 ± 0.1
N	2.54 ± 0.1
R	$0.5R \pm 0.05$

Package Dimension
TO-262
Unit :mm


DIM	MILLIMETERS
A	9.98 ± 0.2
a	7.4 ± 0.4
B	4.5 ± 0.2
b1	1.3 ± 0.05
b2	2.4 ± 0.2
H	23.9 ± 0.3
h	3.1 ± 0.2
h1	9.16 ± 0.2
h2	13.2 ± 0.2
L	0.5 ± 0.1
l1	1.3 ± 0.1
l2	0.8 ± 0.1
N	2.45 ± 0.1

Package Dimension
TO-220F
Unit :mm


DIM	MILLIMETERS
A	10.16 ± 0.3
A1	7.00 ± 0.1
A2	3.3 ± 0.2
A3	9.5 ± 0.2
B1	15.87 ± 0.3
B2	4.7 ± 0.2
B3	6.68 ± 0.4
C	3.3 ± 0.2
C1	12.57 ± 0.3
C2	10.02 ± 0.5
D	2.54 ± 0.05
D1	1.28 ± 0.2
D2	0.8 ± 0.1
K	3.1 ± 0.3
E1	2.54 ± 0.1
E3	0.5 ± 0.1
E4	2.76 ± 0.2
DIA	$\odot 1.5$ (deep 0.2)